

Fig.1 Schematic of ZnO based TFT hydrogen sensor.

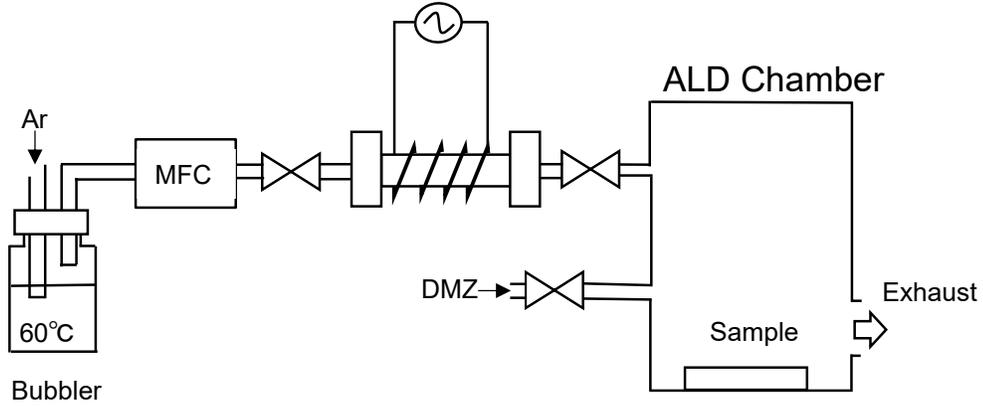


Fig.2 Zinc oxide ALD system.

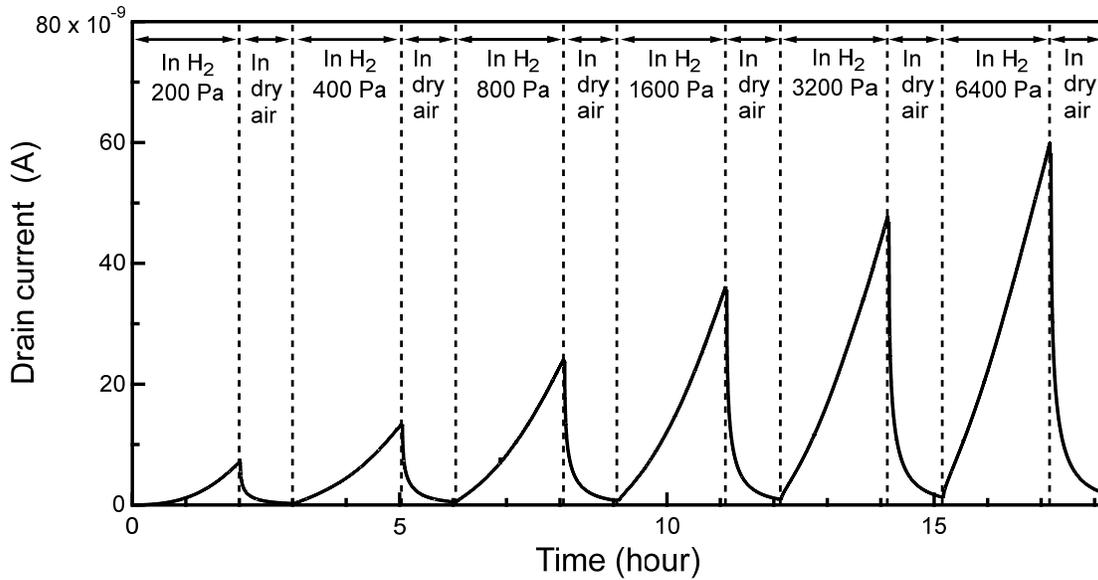


Fig.3 Time variation of the drain current with a ZnO thin film transistor.

The hydrogen partial pressure was increased from 200 to 6400 Pa.

The temperature was in a range from 19.3 to 22.0 °C.